

SPECIFICATION

POLISHING PAD AND METHOD FOR PRODUCING SAME

TECHNICAL FIELD

5 [0001]

The invention relates to a polishing pad capable of performing planarization of materials requiring a high surface planarity such as optical materials including a lens and a reflecting mirror, a silicon wafer, a glass substrate or an aluminum substrates for a hard disc and a product of general metal polishing with stability and a high polishing efficiency. A polishing pad of the invention is preferably employed, especially, in a planarization step of a silicon wafer or a device on which an oxide layer or a metal layer has been formed prior to further stacking an oxide layer or a metal layer thereon.

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15

BACKGROUND ART

[0002]

20 Typical materials requiring surface flatness at high level include a single-crystal silicon disk called a silicon wafer for producing semiconductor integrated circuits (IC, LSI). The surface of the silicon wafer should be flattened highly accurately in a process of producing IC, LSI etc., in order to provide reliable semiconductor connections for various

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coatings used in manufacturing the circuits. In the step of polishing finish, a polishing pad is generally stuck on a rotatable supporting disk called a platen, while a workpiece such as a semiconductor wafer is stuck on a polishing head. By
5 movement of the two, a relative speed is generated between the platen and the polishing head while polishing slurry having abrasive grains is continuously supplied to the polishing pad, to effect polishing processing.

[0003]

10 As polishing characteristics of a polishing pad, it is requested that a polished object is excellent in planarity and within wafer non-uniformity and a polishing rate is large. A planarity and within wafer non-uniformity of a polished object can be improved to some extent with a polishing layer higher
15 in elastic modulus. A polishing rate can be bettered by increasing a holding quantity of a slurry on a foam with cells therein.

[0004]

A polishing pad comprising a non-foamed synthetic resin
20 or a polishing pad comprising a polyurethane foam has been proposed as a polishing pad satisfying the above properties (Patent Documents 1 and 2).

[0005]

However, when a polishing pad comprising a foam is used,
25 there is a problem such that scratches (flaws) are likely to

occur on the surface to be polished of an object to be polished because the contact area between the object to be polished and the polishing pad becomes smaller and local surface pressure becomes higher.

5 [0006]

On the other hand, when planarization process of a large number of semiconductor wafers is performed using a polishing pad, a fine uneven portion of the surface of the polishing pad is worn to deteriorate the performance of supplying a slurry to the processed surface of the semiconductor wafer, to decrease the polishing speed, or to worsen the planarization characteristics. Therefore, after having performed the planarization process of a predetermined number of semiconductor wafers, it is necessary to renew/roughen (dressing) the surface of the polishing pad using a dresser. When dressing is carried out for a predetermined period of time, uncountable fine uneven portions are produced on the surface of the polishing pad, so that the surface of the polishing pad becomes fluffy.

20 [0007]

A conventional non-foamed polishing pad has a problem such that a cut rate is low at the time of dressing and such dressing takes too much time.

25 PRIOR ART DOCUMENTS

PATENT DOCUMENTS

[0008]

Patent Document 1: JP-A-2006-110665

Patent Document 2: JP-B2-4128607

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SUMMARY OF THE INVENTION

PROBLEMS TO BE SOLVED BY THE INVENTION

[0009]

An objective of the present invention is to provide a
10 polishing pad that hardly causes scratches on the surface of
an object to be polished and has an improved dressing property,
and a method for producing the same.

MEANS FOR SOLVING THE PROBLEMS

15 [0010]

As a result of investigations to solve the problems, the
inventors have found that the objects can be achieved with the
polishing pad described below, and have completed the
invention.

20 [0011]

That is, the present invention relates to a polishing pad
having a polishing layer comprising a non-foamed polyurethane,
wherein the non-foamed polyurethane is a reaction cured body
of a polyurethane raw material composition containing an
25 isocyanate-terminated prepolymer obtained by reacting a

prepolymer raw material composition containing a diisocyanate,
a high-molecular-weight polyol and a low-molecular-weight
polyol; an isocyanate modified body polymerized by adding three
or more diisocyanates; and a chain extender, and the addition
5 amount of the isocyanate-modified body is 5 to 30 parts by weight
with respect to 100 parts by weight of the isocyanate-terminated
prepolymer.

[0012]

The present invention is characterized by forming a
10 polishing layer with a non-foamed polyurethane. It is possible
to thereby effectively suppress the occurrence of scratches on
the surface to be polished because the contact area between an
object to be polished and a polishing layer becomes larger and
surface pressure applied to the object to be polished becomes
15 lower and uniform.

[0013]

Further, the present inventors have found that the
surface of a polishing pad is easily renewed because partial
introduction of chemical crosslinking into a polymer (partial
20 formation of a three-dimensional crosslinked structure) as a
result of the reaction between the chain extender and a
combination of the isocyanate-terminated prepolymer and the
isocyanate-modified body polymerized by adding three or more
diisocyanate as the non-foamed polyurethane raw material makes
25 the non-foamed polyurethane hard and brittle to allow the cut

rate at the time of dressing increase. In addition, by allowing the isocyanate-modified body to directly react with the chain extender instead of introducing into the isocyanate-terminated prepolymer, it is possible to introduce regular chemical
5 crosslinking in the polymer. Thus, brittleness in the entire surface of the polishing layer can be made uniform, so that variation in abrasion can be suppressed.

[0014]

The high-molecular-weight polyol is preferably a
10 polyether polyol having a number average molecular weight of 500 to 5000, and the diisocyanate is preferably toluene diisocyanate and dicyclohexylmethane diisocyanate. In addition, the isocyanate-modified body is preferably a hexamethylene diisocyanate-modified body of isocyanurate type
15 and/or biuret type. By using these substances, swelling of the non-foamed polyurethane at the time of absorbing water is suppressed, and renewability of the pad surface is improved at the time of dressing.

[0015]

20 It is necessary to add 5 to 30 parts by weight of the isocyanate-modified body with respect to 100 parts by weight of the isocyanate-terminated prepolymer. When the addition amount of the isocyanate-modified body is less than 5 parts by weight, renewability of the pad surface at the time of dressing
25 is reduced and the non-foamed polyurethane becomes easy to swell

at the time of absorbing water because of insufficient ratio of the chemical crosslinking in the polymer. On the other hand, when it exceeds 30 parts by weight, scratches are likely to occur on the surface of the object to be polished because the ratio
5 of the chemical crosslinking in the polymer becomes excessive and the hardness of the non-foamed polyurethane becomes too high.

[0016]

In addition, the non-foamed polyurethane has preferably
10 an Asker D hardness of 65 to 80 degrees. When the Asker D hardness is less than 65 degrees, the planarity of the object to be polished tends to be reduced. On the other hand, when it is greater than 80 degrees, the planarity is good, but the in-plane uniformity of the object to be polished tends to be
15 reduced. In addition, scratches are more likely to occur on the surface of the object to be polished.

[0017]

Further, from the viewpoint of renewability of the pad surface, the cut rate of the polishing pad of the present
20 invention is preferably 2 $\mu\text{m}/\text{minute}$ or more.

[0018]

Moreover, the present invention relates to a method for producing a polishing pad, comprising the step of mixing a first component containing 5 to 30 parts by weight of an
25 isocyanate-modified body polymerized by adding three or more

diisocyanates with respect to 100 parts by weight of an isocyanate-terminated prepolymer obtained by reacting a prepolymer raw material composition containing a diisocyanate, a high-molecular-weight polyol and a low-molecular-weight polyol, with a second component containing a chain extender; and curing the mixture to prepare a non-foamed polyurethane.

[0019]

The invention is also related to a method for manufacturing a semiconductor device, including the step of polishing a surface of a semiconductor wafer using the polishing pad.

BRIEF DESCRIPTION OF THE DRAWINGS

[0020]

Fig. 1 is a schematic diagram showing a typical polishing apparatus for use in CMP polishing; and

Fig. 2 is a schematic diagram showing 73 points on a wafer at each of which the film thickness is measured.

MODE FOR CARRYING OUT THE INVENTION

[0021]

The polishing pad of the invention includes a polishing layer including a non-foamed polyurethane. The polishing pad of the invention may be only the polishing layer or a laminated body of the polishing layer and any other layer (such as a cushion

layer).

[0022]

Polyurethane is a preferred material for forming the polishing layer, because polyurethane is excellent in abrasion
5 resistance and polymers with desired physical properties can be easily obtained by varying the raw material composition.

[0023]

The non-foamed polyurethane is a reaction cured body of a polyurethane raw material composition containing an
10 isocyanate-terminated prepolymer obtained by reacting a prepolymer raw material composition containing a diisocyanate, a high-molecular-weight polyol and a low-molecular-weight polyol; an isocyanate-modified body polymerized by adding three or more diisocyanates; and a chain extender.

15 [0024]

As the diisocyanate, a compound known in the field of polyurethane can be used without particular limitation. The isocyanate monomer includes, for example, aromatic diisocyanates such as 2,4-toluene diisocyanate, 2,6-toluene
20 diisocyanate, 2,2'-diphenyl methane diisocyanate, 2,4'-diphenyl methane diisocyanate, 4,4'-diphenyl methane diisocyanate, 1,5-naphthalene diisocyanate, p-phenylene diisocyanate, m-phenylene diisocyanate, p-xylylene diisocyanate and m-xylylene diisocyanate, aliphatic
25 diisocyanates such as ethylene diisocyanate, 2,2,4-trimethyl

hexamethylene diisocyanate and 1,6-hexamethylene diisocyanate, and cycloaliphatic diisocyanates such as 1,4-cyclohexane diisocyanate, 4,4'-dicyclohexyl methane diisocyanate, isophorone diisocyanate and norbornane diisocyanate. These
5 may be used alone or as a mixture of two or more thereof. Among the above isocyanate monomers, toluene diisocyanate and dicyclohexylmethane diisocyanate are preferably used in combination.

[0025]

10 As used herein, the term 'isocyanate-modified body' refers to any of polymerized compounds produced by addition of three or more molecules of diisocyanate, or refers to a mixture of the compounds. For example, the isocyanate-modified body may be of (1) trimethylolpropane adduct type, (2) biuret type,
15 (3) isocyanurate type, or the like. In particular, the isocyanurate type or the biuret type is preferred.

[0026]

In the invention, the isocyanate-modified body is preferably produced using aliphatic diisocyanate,
20 specifically 1,6-hexamethylene diisocyanate. The isocyanate-modified body may also be a modification such as a urethane-modified, allophanate-modified, or biuret-modified body.

[0027]

25 As the high-molecular-weight polyol, those usually used

in the art of polyurethane can be exemplified. Examples thereof include polyether polyols represented by polytetramethylene ether glycol and polyethylene glycol; polyester polyols represented by polybutylene adipate; polyester polycarbonate polyols exemplified by reaction products of polyester glycol such as polycaprolactone polyol or polycaprolactone and alkylene carbonate; polyester polycarbonate polyols obtained by reacting ethylene carbonate with polyvalent alcohol and the reacting the resultant reaction mixture with an organic dicarboxylic acid; and polycarbonate polyols obtained by ester exchange reaction between polyhydroxyl compound and aryl carbonate. These may be used singly or in combination of two or more kinds.

[0028]

The number average molecular weight of the high-molecular-weight polyol is not particularly limited, but it is preferably 500 to 5000, and more preferably 1000 to 2000, from the viewpoint of the elastic properties of the obtained polyurethane and the like. If the number average molecular weight is less than 500, the number of hard segment becomes too many, resulting in giving polyurethane with low toughness. On the other hand, if the number average molecular weight is more than 5000, the polyurethane becomes too soft and a polishing pad made from the polyurethane tends to have poor planarization properties.

[0029]

Examples of the low-molecular-weight polyol include ethylene glycol, 1,2-propylene glycol, 1,3-propylene glycol, 1,2-butanediol, 1,3-butanediol, 1,4-butanediol, 5 2,3-butanediol, 1,6-hexanediol, neopentyl glycol, 1,4-cyclohexanedimethanol, 3-methyl-1,5-pentanediol, diethylene glycol, triethylene glycol, 1,4-bis(2-hydroxyethoxy)benzene, trimethylolpropane, glycerin, 1,2,6-hexanetriol, pentaerythritol, 10 tetramethylolcyclohexane, methylglucoside, sorbitol, mannitol, dulcitol, sucrose, 2,2,6,6-tetrakis(hydroxymethyl)cyclohexanol, diethanolamine, N-methyldiethanolamine, and triethanolamine. One or more of these polyols may be used alone or in any combination.

15 [0030]

A low-molecular-weight polyamine such as ethylenediamine, tolylenediamine, diphenylmethanediamine, or diethylenetriamine may also be used as a raw material for the isocyanate-terminated prepolymer concomitantly. An 20 alcoholamine such as monoethanolamine, 2-(2-aminoethylamino)ethanol, or monopropanolamine may also be used concomitantly. These materials may be used alone or one or more of these may be used concomitantly.

[0031]

25 The amount of the low-molecular-weight polyol, the

low-molecular-weight polyamine, or the like is, although not limited particularly, preferably from 20 to 70% by mole, based on the amount of full active hydrogen group-containing compounds used as raw materials for the isocyanate-terminated prepolymer, while it may be appropriately determined depending on the desired properties of the polishing pad (polishing layer) to be produced.

[0032]

A chain extender is an organic compound having at least two active hydrogen groups and examples of the active hydrogen group include: a hydroxyl group, a primary or secondary amino group, a thiol group (SH) and the like. Concrete examples of the chain extender include: polyamines such as 4,4'-methylenebis(o-chloroaniline) (MOCA), 2,6-dichloro-p-phenylenediamine, 4,4'-methylenebis(2,3-dichloroaniline), 3,5-bis(methylthio)-2,4-toluenediamine, 3,5-bis(methylthio)-2,6-toluenediamine, 3,5-diethyltoluene-2,4-diamine, 3,5-diethyltoluene-2,6-diamine, trimethylene glycol-di-p-aminobenzoate, polytetramethylene oxide-di-p-aminobenzoate, 4,4'-diamino-3,3',5,5'-tetraethyldiphenylmethane, 4,4'-diamino-3,3'-diisopropyl-5,5'-dimethyldiphenylmethane, 4,4'-diamino-3,3',5,5'-tetraisopropyldiphenylmethane,

1,2-bis(2-aminophenylthio)ethane,
4,4'-diamino-3,3'-diethyl-5,5'-dimethyldiphenylmethane,
N,N'-di-sec-butyl-4,4'-diaminophenylmethane,
3,3'-diethyl-4,4'-diaminodiphenylmethane, m-xylylenediamine,
5 N,N'-di-sec-butyl-p-phenylenediamine, m-phenylenediamine and
p-xylylenediamine; the low-molecular-weight polyol; and the
low-molecular-weight polyamine. The chain extenders
described above may be used either alone or in mixture of two
kinds or more.

10 [0033]

It is necessary to add 5 to 30 parts by weight, preferably
5 to 20 parts by weight, of the isocyanate-modified body with
respect to 100 parts by weight of the isocyanate-terminated
prepolymer. Further, in order to obtain polishing pad having
15 desired polishing properties, the number of isocyanate groups
in the isocyanate components is preferably from 0.80 to 1.20,
more preferably from 0.99 to 1.15 per the number of active
hydrogen groups (hydroxyl groups and/or amino groups) in the
chain extender. If the number of isocyanate groups is outside
20 the range, insufficient curing could occur so that the required
specific gravity or hardness could not be achieved, which tends
to decrease the polishing properties.

[0034]

The non-foamed polyurethane is preferably produced by
25 melting method in view of cost, working environment and so on,

while it may be produced by application of any known urethane foaming techniques such as melting method and solution technique. Various additives may be mixed; such as a stabilizer including an antioxidant, a lubricant, a pigment, a filler, an
5 antistatic agent and others.

[0035]

A known catalyst promoting polyurethane reaction, such as tertiary amine-based catalysts, may be used. The type and amount of the catalyst added are determined in consideration
10 of flow time in casting in a predetermined mold after the mixing step.

[0036]

Production of the non-foamed polyurethane may be in a batch system where each component is weighed out, introduced
15 into a vessel and mixed or in a continuous production system where each component is continuously supplied to, and stirred in, a stirring apparatus and a polyurethane raw material composition is transferred to produce molded articles.

[0037]

20 A manufacturing method of a polishing pad may be performed in ways: in one of which an isocyanate-terminated prepolymer and an isocyanate modified body are put into a reaction vessel, thereafter a chain extender is mixed into the reaction vessel, the mixture is agitated, thereafter the mixture is cast into a
25 mold with a predetermined size to thereby prepare a block and

the block is sliced with a slicer like a planer or a band saw;
and in another of which in the step of casting into the mold,
a thin sheet may be directly produced. Besides, a still another
way may be adopted in which a resin of raw material is melted,
5 the melt is extruded through a T die to thereby mold a non-foamed
polyurethane directly in the shape of a sheet.

[0038]

The non-foamed polyurethane has preferably an Asker D
hardness of 65 to 80 degrees, and more preferably 70 to 75
10 degrees.

[0039]

A polishing pad (polishing layer) of the invention is
preferably provided with a depression and a protrusion
structure for holding and renewing a slurry. Though in a case
15 where the polishing layer is formed with a non-foamed body,
which lacks in work to hold and renew the slurry, a depression
and protrusion structure are preferably provided on the surface
of the polishing side thereof in order to achieve more of
holdability and renewal of the slurry or in order to prevent
20 induction of dechuck error or breakage of an object to be
polished. The shape of the depression and protrusion structure
is not particularly limited insofar as slurry can be retained
and renewed, and examples include latticed grooves, concentric
circle-shaped grooves, through-holes, non-through-holes,
25 polygonal prism, cylinder, spiral grooves, eccentric grooves,

radial grooves, and a combination of these grooves. The groove pitch, groove width, groove thickness etc. are not particularly limited either, and are suitably determined to form grooves. These depression and protrusion structure are generally those
5 having regularity, but the groove pitch, groove width, groove depth etc. can also be changed at each certain region to make retention and renewal of slurry desirable.

[0040]

The method of forming the depression and protrusion
10 structure is not particularly limited, and for example, formation by mechanical cutting with a jig such as a bite of predetermined size, formation by casting and curing resin in a mold having a specific surface shape, formation by pressing resin with a pressing plate having a specific surface shape,
15 formation by photolithography, formation by a printing means, and formation by a laser light using a CO₂ gas laser or the like.

[0041]

No specific limitation is placed on a thickness of a polishing layer, but a thickness thereof is about 0.8 to 4 mm, preferably 1.5 to 2.5 mm. The method of preparing the polishing
20 layer of this thickness includes a method wherein a block of the non-foamed polyurethane is cut in predetermined thickness by a slicer in a bandsaw system or a planing system, a method that involves casting resin into a mold having a cavity of
25 predetermined thickness and curing the resin, a method of using

coating techniques and sheet molding techniques, etc.

[0042]

The scatter of the thickness of the polishing layer is preferably 100 μm or less. When the scatter of the thickness is higher than 100 μm , large undulation is caused to generate portions different in a contacting state with an object to be polished, thus adversely influencing polishing characteristics. To solve the scatter of the thickness of the polishing layer, the surface of the polishing layer is dressed generally in an initial stage of polishing by a dresser having abrasive grains of diamond deposited or fused thereon, but the polishing layer outside of the range described above requires a longer dressing time to reduce the efficiency of production.

[0043]

As a method of suppressing the scatter of thickness, there is also a method of buffing the surface of the polishing layer having a predetermined thickness. Buffing is conducted preferably stepwise by using polishing sheets different in grain size.

[0044]

A polishing pad of the invention may also be a laminate of a polishing layer and a cushion layer adhered to each other.

[0045]

The cushion layer compensates for characteristics of the polishing layer. The cushion layer is required for satisfying

both planarity and uniformity which are in a tradeoff relationship in CMP. Planarity refers to flatness of a pattern region upon polishing an object to be polished having fine unevenness generated upon pattern formation, and uniformity
5 refers to the uniformity of the whole of an object to be polished. Planarity is improved by the characteristics of the polishing layer, while uniformity is improved by the characteristics of the cushion layer. The cushion layer used in the polishing pad of the present invention is preferably softer than the polishing
10 layer.

[0046]

The material forming the cushion layer is not particularly limited, and examples of such material include a nonwoven fabric such as a polyester nonwoven fabric, a nylon
15 nonwoven fabric or an acrylic nonwoven fabric, a nonwoven fabric impregnated with resin such as a polyester nonwoven fabric impregnated with polyurethane, polymer resin foam such as polyurethane foam and polyethylene foam, rubber resin such as butadiene rubber and isoprene rubber, and photosensitive resin.

20 [0047]

Means for adhering the polishing layer to the cushion layer include: for example, a method in which a double sided tape is sandwiched between the polishing layer and the cushion layer, followed by pressing.

25 [0048]

The double sided tape is of a common construction in which adhesive layers are provided on both surfaces of a substrate such as a nonwoven fabric or a film. It is preferable to use a film as a substrate with consideration given to prevention of permeation of a slurry into a cushion layer. A composition of an adhesive layer is, for example, of a rubber-based adhesive, an acrylic-based adhesive or the like. An acrylic-based adhesive is preferable because of less of a content of metal ions, to which consideration is given. Since a polishing layer and a cushion layer is sometimes different in composition from each other, different compositions are adopted in respective adhesive layers of double sided tape to thereby also enable adhesive forces of the respective adhesive layers to be adjusted to proper values.

[0049]

A polishing pad of the invention may be provided with a double sided tape on the surface of the pad adhered to a platen. As the double sided tape, a tape of a common construction can be used in which adhesive layers are, as described above, provided on both surfaces of a substrate. As the substrate, for example, a nonwoven fabric or a film is used. Preferably used is a film as a substrate since separation from the platen is necessary after the use of a polishing pad. As a composition of an adhesive layer, for example, a rubber-based adhesive or an acrylic-based adhesive is exemplified. Preferable is an

acrylic-based adhesive because of less of metal ions in content to which consideration is given.

[0050]

A semiconductor device is fabricated after operation in
5 a step of polishing a surface of a semiconductor wafer with a
polishing pad. The term, a semiconductor wafer, generally
means a silicon wafer on which a wiring metal and an oxide layer
are stacked. No specific limitation is imposed on a polishing
method of a semiconductor wafer or a polishing apparatus, and
10 polishing is performed with a polishing apparatus equipped, as
shown in Fig. 1, with a polishing platen 2 supporting a polishing
pad (a polishing layer) 1, a polishing head 5 holding a
semiconductor wafer 4, a backing material for applying a uniform
pressure against the wafer and a supply mechanism of a polishing
15 agent 3. The polishing pad 1 is mounted on the polishing platen
2 by adhering the pad to the platen with a double sided tape.
The polishing platen 2 and the polishing head 5 are disposed
so that the polishing pad 1 and the semiconductor wafer 4
supported or held by them oppositely face each other and
20 provided with respective rotary shafts 6 and 7. A pressure
mechanism for pressing the semiconductor wafer 4 to the
polishing pad 1 is installed on the polishing head 5 side.
During polishing, the semiconductor wafer 4 is polished by being
pressed against the polishing pad 1 while the polishing platen
25 2 and the polishing head 5 are rotated and a slurry is fed. No

specific limitation is placed on a flow rate of the slurry, a polishing load, a polishing platen rotation number and a wafer rotation number, which are properly adjusted.

[0051]

5 Protrusions on the surface of the semiconductor wafer 4 are thereby removed and polished flatly. Thereafter, a semiconductor device is produced therefrom through dicing, bonding, packaging etc. The semiconductor device is used in an arithmetic processor, a memory etc.

10

Examples

[0052]

Description will be given of the invention with examples, while the invention is not limited to description in the
15 examples.

[0053]

[Measurement and Evaluation Method]

(Measurement of Number-Average Molecular Weight)

A number-average molecular weight was measured by GPC (a
20 Gel Permeation Chromatography) and a value as measured was converted in terms of standard polystyrene molecular weight, and the apparatus and conditions in operation were as follows:

GPC apparatus was an apparatus manufactured by Shimadzu Corp., with Model Number of LC-10A.

25 Columns that were used in measurement were ones

manufactured by Polymer Laboratories Co., in which three columns were in connection including (PL gel, 5 μm and 500 $\text{\AA}$), (PL gel, 5 μm and 100 $\text{\AA}$) and (PL gel, 5 μm and 50 $\text{\AA}$).

A flow rate was 1.0 ml/min.

5 A concentration was 1.0 g/l.

An injection quantity was 40 μl .

A column temperature was 40°C.

An eluent was tetrahydrofuran.

[0054]

10 (Measurement of specific gravity)

Determined according to JIS Z8807-1976. A manufactured non-foamed polyurethane and a manufactured polyurethane foam cut out in the form of a strip of 4 cm $\times$ 8.5 cm (thickness: arbitrary) was used as a sample for measurement of specific gravity and left for 16 hours in an environment of a temperature of 23 $\pm$ 2°C and a humidity of 50% $\pm$ 5%. Measurement was conducted by using a specific gravity hydrometer (manufactured by Sartorius Co., Ltd).

[0055]

20 (Measurement of hardness)

Measurement is conducted according to JIS K6253-1997. A manufactured non-foamed polyurethane and a manufactured polyurethane foam cut out in a size of 2 cm $\times$ 2 cm (thickness: arbitrary) was used as a sample for measurement of hardness and left for 16 hours in an environment of a temperature of 23 $\pm$ 2°C

and a humidity of 50%±5%. At the time of measurement, samples were stuck on one another to a thickness of 6 mm or more. A hardness meter (Asker D hardness meter, manufactured by Kobunshi Keiki Co., Ltd.) was used to measure hardness.

5 [0056]

(Measurement of surface roughness distribution)

A prepared polishing pad was bonded to a platen of a polishing apparatus (SPP600S, manufactured by Okamoto Machine Tool Works, Ltd.). Using a dresser (M type, manufactured by
10 Asahi Diamond Industrial Co., Ltd.), the surface of a polishing layer was dressed under the conditions of a dressing pressure of 50 g/cm², a platen rotation speed of 35 rpm, a water flow of 200 ml/minute, and a dressing time of 30 minutes. After completion of the dressing, at the central position in the
15 radial direction of the polishing pad, three samples (20 mm × 20 mm) were cut at intervals of 120°. Using a stylus profilometer (P-15, manufactured by KLA Tencor Japan Ltd.), each surface roughness of the three samples was measured once and each three-dimensional square root roughness Sq (μm) of the
20 surface was calculated. Then the mean value of the Sq values of the three samples (mean Sq value) was calculated. The mean Sq value is preferably 6 to 9 μm. The three-dimensional square root roughness Sq is determined by the following expression when the XY plane represents the average plane, the Z-axis represents
25 the vertical direction, and the measured curve of surface shape

is expressed by $z=f(x,y)$:

[Mathematical expression 1]

$$Sq = \sqrt{\frac{1}{L_x L_y} \int_0^{L_x} \int_0^{L_y} f^2(x,y) dx dy}$$

wherein L_x is a measuring length in the x-direction, and

5 L_y is a measuring length in the y-direction.

Measurement conditions

Measurement area: 500 μm $\times$ 500 μm (measuring length 500 μm)

Scanning speed: Scan pitch 20 $\mu\text{m}/\text{second}$

Trace: 51 (10 μm pitch)

10 Measurement load: 2 mg

[0057]

(Measurement of cut rate)

A prepared polishing pad was bonded to a platen of a polishing apparatus (SPP600S, manufactured by Okamoto Machine
15 Tool Works, Ltd.). Using a dresser (M type, manufactured by Asahi Diamond Industrial Co., Ltd.), the surface of a polishing layer was dressed under the conditions of a dressing load of 9.7 lbf, a dressing pressure of 50 g/cm², a platen rotation speed of 35 rpm, a water flow of 200 ml/minute, and a dressing time
20 of 30 minutes. After completion of the dressing, a strip sample (20 mm in width $\times$ 610 mm in length) was cut out therefrom. The thickness of the sample was measured at points spaced at intervals of 20 mm from the central part (15 points on one side, 30 points in total). The difference (abrasion loss) between

the thickness of non-dressed central part and the thickness of each measurement point was calculated, and then the average of the differences was calculated. The cut rate is calculated from the following equation. In the present invention, the cut rate
5 is preferably 2 $\mu\text{m}/\text{minute}$ or more, and more preferably 2 to 3 $\mu\text{m}/\text{minute}$.

Cut rate ($\mu\text{m}/\text{minute}$) = average of abrasion loss / (0.5 x
60)

[0058]

10 (Evaluation of scratches)

Evaluation of scratches was carried out by using a polishing apparatus SPP600S (manufactured by Okamoto Machine Tool Works, Ltd.) with use of a prepared polishing pad. After polishing an 8-inch silicon wafer having a 1 μm -thick thermal
15 oxide film formed thereon under the following conditions, the number of defects of 0.19 to 2 μm in the wafer was measured at an EE (edge exclusion) of 5 mm by using a surface defect detector (Surf Scan SP1 TBI, manufactured by KLA-Tencor Japan, Ltd.). The polishing conditions were as follows: a silica slurry (SS12,
20 manufactured by Cabot) was added at a flow rate of 150 ml/minute during polishing, the polishing load was 350 g/cm^2 , the polishing platen rotation speed was 35 rpm, and the wafer rotation speed was 30 rpm.

[0059]

25 (Measurement of average polishing speed)

Measurement of average polishing speed was carried out by using a polishing apparatus SPP600S (manufactured by Okamoto Machine Tool Works, Ltd.) with use of a prepared polishing pad. An 8-inch silicon wafer having a 1 μm -thick thermal oxide film formed thereon was polished for one minute under the following conditions. As shown in Fig. 2, average polishing speed was calculated from the film thickness measured at specific 73 points on the wafer after the polishing. The thickness of the oxide film was measured with use of an interference type film thickness measuring apparatus (manufactured by Otsuka Electronics Co., Ltd.). The polishing conditions were as follows: a silica slurry (SS12, manufactured by Cabot) was added at a flow rate of 150 ml/minute during polishing, the polishing load was 350 g/cm², the polishing platen rotation speed was 35 rpm, and the wafer rotation speed was 30 rpm.

[0060]

Example 1

To a vessel were added 1229 parts by weight of toluene diisocyanate (a mixture of toluene 2,4-diisocyanate/toluene 2,6-diisocyanate = 80/20), 272 parts by weight of 4,4'-dicyclohexylmethane diisocyanate, 1901 parts by weight of polytetramethylene ether glycol with a number average molecular weight of 1018, and 198 parts by weight of diethylene glycol, and the mixture was allowed to react at 70°C for 4 hours to obtain an isocyanate-terminated prepolymer. One hundred parts by

weight of the prepolymer and 10 parts by weight of a polymerized 1,6-hexamethylene diisocyanate (Sumijule N-3300 (isocyanurate type) manufactured by Sumika Bayer Urethane Co., Ltd.) were mixed in a planetary mixing and defoaming apparatus and defoamed.

5 After that, 32.9 parts by weight of 4,4'-methylenebis(o-chloroaniline) which had been melted at 120°C was added to the mixture and mixed in the planetary mixing and defoaming apparatus, and then defoamed to prepare a polyurethane raw material composition. The composition was

10 poured into an open mold (800 mm in length and width and 2.5 mm in depth) (casting vessel) and post curing was performed at 100°C for 16 hours to obtain a non-foamed polyurethane sheet. The surface of the sheet was then buffed with a buffing machine (manufactured by AMITEC) until the sheet had a thickness of 1.27

15 mm. As a result, the sheet had adjusted thickness accuracy. The buffed sheet was punched out to form a disc with a diameter of 61 cm, and processing of concentric circular grooves each with a width of 0.25 mm and a depth of 0.40 mm at a groove pitch of 1.50 mm was performed on the surface of the sheet using a

20 grooving machine (manufactured by Techno) so that a polishing layer was obtained. A double-faced adhesive tape (Double Tack Tape manufactured by SEKISUI CHEMICAL CO., LTD.) was bonded to the surface of the polishing layer opposite to the grooved surface using a laminator. The surface of a corona-treated

25 cushion layer (Toraypef (0.8 μ m-thick polyethylene foam),

manufactured by Toray Industries, Inc.) was buffed. The buffed cushion layer was bonded to the double-faced adhesive tape using a laminator. Another double-faced adhesive tape was also bonded to the other side of the cushion layer using a laminator
5 so that a polishing pad was prepared.

[0061]

Example 2

A polishing pad was prepared in the same manner as in Example 1, except that in Example 1, the addition amount of
10 Sumijule N-3300 was changed to 5 parts by weight from 10 parts by weight and the addition amount of 4,4'-methylenebis(o-chloroaniline) was changed to 29.7 parts by weight from 32.9 parts by weight.

[0062]

15 Example 3

A polishing pad was prepared in the same manner as in Example 1, except that in Example 1, 10 parts by weight of a polymerized 1,6-hexamethylene diisocyanate (Sumijule N-3200, biuret type, manufactured by Sumika Bayer Urethane Co., Ltd.)
20 as an isocyanate-modified body was used in place of Sumijule N-3300, and the addition amount of 4,4'-methylenebis(o-chloroaniline) was changed to 33.2 parts by weight from 32.9 parts by weight.

[0063]

25 Comparative Example 1

A polishing pad was prepared in the same manner as in Example 1, except that in Example 1, Sumijule N-3300 was not added and the addition amount of 4,4'-methylenebis(o-chloroaniline) was changed to 26.6 parts by weight from 32.9 parts by weight.

[0064]

Comparative Example 2

A polishing pad was prepared in the same manner as in Example 1, except that in Example 1, the addition amount of Sumijule N-3300 was changed to 35 parts by weight from 10 parts by weight, and the addition amount of 4,4'-methylenebis(o-chloroaniline) was changed to 48.8 parts by weight from 32.9 parts by weight.

[0065]

Comparative Example 3

To a vessel were added 1229 parts by weight of toluene diisocyanate (a mixture of toluene 2,4-diisocyanate/toluene 2,6-diisocyanate = 80/20), 272 parts by weight of 4,4'-dicyclohexylmethane diisocyanate, 1901 parts by weight of polytetramethylene ether glycol with a number average molecular weight of 1018, and 198 parts by weight of diethylene glycol, and the mixture was allowed to react at 70°C for 4 hours to obtain an isocyanate-terminated prepolymer. One hundred parts by weight of the prepolymer, 20 parts by weight of a polymerized 1,6-hexamethylene diisocyanate (Sumijule N-3300 (isocyanurate

type) manufactured by Sumika Bayer Urethane Co., Ltd.), and 3.6 parts by weight of a silicon-based surfactant (SH-192, manufactured by Dow Corning Toray Silicone Co., Ltd.) were added to a polymerization vessel and mixed, and the mixture was
5 adjusted to 80°C, and then defoamed under reduced pressure. The mixture was vigorously agitated at a rotation number of 900 rpm for about 4 minutes with agitation blades so that bubbles were incorporated into the reaction system. To the reaction system was added 39.3 parts by weight of
10 4,4'-methylenebis(o-chloroaniline) that had been melted at 120°C in advance. The mixture liquid was agitated for about 70 seconds and then poured into a pan type open mold (casting vessel). At the time when the mixture liquid lost fluidity, it was put into an oven and post-cured at 100°C for 16 hours
15 to obtain a polyurethane foam block. The polyurethane foam block heated at about 80°C was sliced with a slicer (VGW-125, manufactured by AMITEC) to obtain a polyurethane foam sheet. The surface of the sheet was then buffed with a buffing machine (manufactured by AMITEC) until the sheet had a thickness of 1.27
20 mm. As a result, the sheet had adjusted thickness accuracy. The buffed sheet was punched out to form a disc with a diameter of 61 cm, and processing of concentric circular grooves each with a width of 0.25 mm and a depth of 0.40 mm at a groove pitch of 1.50 mm was performed on the surface of the sheet using a
25 grooving machine (manufactured by Techno) so that a polishing

layer was obtained. Then, a polishing pad was prepared in the same manner as in Example 1.

[0066]

[Table 1]

	Specific gravity	D hardness (degree)	Three-dimensional square root roughness Mean Sq value (μm)	Cut rate ($\mu\text{m}/\text{minute}$)	Scratch (number)	Average polishing speed (angstrom/minute)
Example 1	1.1	73.5	7.6	2.8	32	2100
Example 2	1.1	70.5	6.5	2.1	40	2040
Example 3	1.1	73.0	7.5	2.7	30	2080
Comparative Example 1	1.1	69.0	5.1	0.8	73	1800
Comparative Example 2	1.1	82.0	5.5	4.0	310	1850
Comparative Example 3	0.86	61.0	11.0	3.4	100	2100

5

DESCRIPTION OF REFERENCE SIGNS

[0067]

- 1: Polishing pad (polishing layer)
- 2: Polishing platen
- 10 3: Polishing agent (slurry)
- 4: Object to be polished (semiconductor wafer)
- 5: Supporting stand (polishing head)
- 6, 7: Rotary shaft

The invention claimed is:

1. A polishing pad having a polishing layer comprising a non-foamed polyurethane, wherein the non-foamed polyurethane is a reaction cured body of a polyurethane raw material composition containing an isocyanate-terminated prepolymer obtained by reacting a prepolymer raw material composition containing a diisocyanate, a high-molecular-weight polyol and a low-molecular-weight polyol; an isocyanate modified body polymerized by adding three or more diisocyanates; and a chain extender, and the addition amount of the isocyanate-modified body is 5 to 30 parts by weight with respect to 100 parts by weight of the isocyanate-terminated prepolymer, wherein a cut rate which is a dressed amount (μm) per minute of the polishing layer by dressing the polishing layer is $2\ \mu\text{m}/\text{minute}$ or more.

2. The polishing pad according to claim 1, wherein the high-molecular-weight polyol is a polyether polyol having a number average molecular weight of 500 to 5000, and the diisocyanates is toluene diisocyanate and dicyclohexylmethane diisocyanate.

3. The polishing pad according to claim 1, wherein the isocyanate-modified body is a hexamethylene diisocyanate-modified body of isocyanurate type and/or biuret type.

4. The polishing pad according to claim 1, wherein the non-foamed polyurethane has an Asker D hardness of 65 to 80 degrees.

5. A method for producing a polishing pad, comprising the step of mixing a first component containing 5 to 30 parts by weight of an isocyanate-modified body polymerized by adding three or more diisocyanates with respect to 100 parts by weight of an isocyanate-terminated prepolymer obtained by

reacting a prepolymer raw material composition containing a diisocyanate, a high-molecular-weight polyol and a low-molecular-weight polyol, with a second component containing a chain extender; and curing the mixture to prepare a non-foamed polyurethane.

6. A method for producing a semiconductor device, comprising the step of polishing the surface of a semiconductor wafer by using the polishing pad according to claim 1.

7. The polishing pad according to claim 1, wherein the cut rate is between 2 and 3 $\mu\text{m}/\text{minute}$.